

TENTATIVE

TOSHIBA PHOTOCOUPLER GaAs IRED + PHOTO-TRIAC

TLP763JF

OFFICE MACHINE
 HOUSEHOLD USE EQUIPMENT
 TRIAC DRIVER
 SOLID STATE RELAY

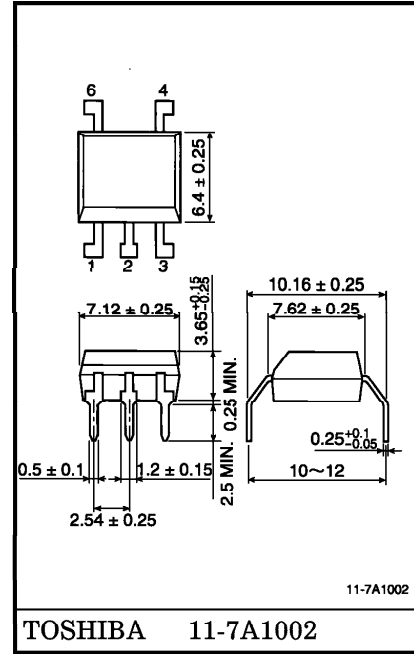
Unit in mm

The TOSHIBA TLP763JF consists of a GaAs infrared LED optically coupled to a zero voltage crossing turn-on photo-triac in a 6 lead plastic DIP.

- Peak Off-State Voltage : 600V (MIN.)
 - Trigger LED Current : 10mA (MAX.)
 - On-State Current : 100mA (MAX.)
 - UL Recognized : UL1577, File No. E67349
 - BSI Approved : BS EN60065 : 1994,
 Certificate No. 7831
 BS EN60950 : 1992,
 Certificate No. 7832
 - SEMKO Approved : SS-EN60065 (EN60065, 1993)
 SS-EN60950 (EN60950, 1992)
 SS-EN60335 (EN60335, 1988)
 Certificate No. 9522145
 - Isolation Voltage : 4000Vrms (Min.)
 - Option (D4) type VDE Approved : DIN VDE0884 / 06.92,
 Certificate No. 91803
- Maximum Operating Insulation Voltage : 1130V_{PK}
 Highest Permissible Over Voltage : 6000V_{PK}

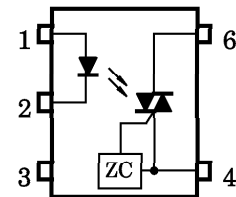
(Note) When a VDE0884 approved type is needed, please designate the "Option (D4)"

- Creepage Distance : 8.0mm (Min.)
- Clearance : 8.0mm (Min.)
- Internal Creepage Path : 4.0mm (Min.)
- Insulation Thickness : 0.4mm (Min.)



Weight : 0.42g

PIN CONFIGURATION (TOP VIEW)



- 1 : ANODE
- 2 : CATHODE
- 3 : NC
- 4 : TRIAC 1
- 6 : TRIAC 2

Please refer to the technical data of TLP763J for **MAXIMUM RATINGS** and **ELECTRICAL CHARACTERISTICS**.

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